Electronic Supplementary Material (ESI) for RSC Advances.

Semiconductor and topological phases in lateral heterostructures constructed from germanene and AsSb monolayers

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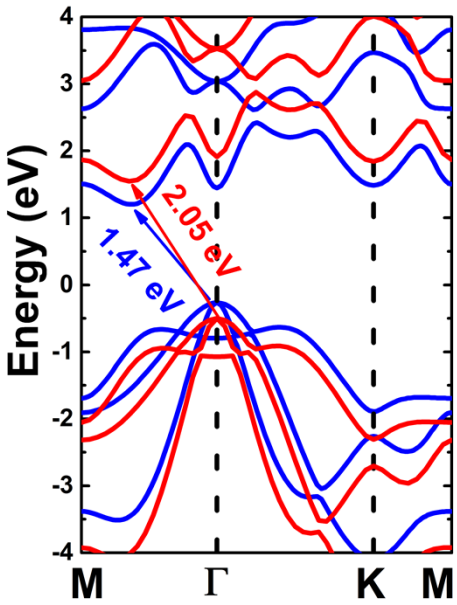

Figure S1: Electronic band structure of AsSb monolayer calculated with PBE (blue curve) and HSE06 (red curve) functionals.

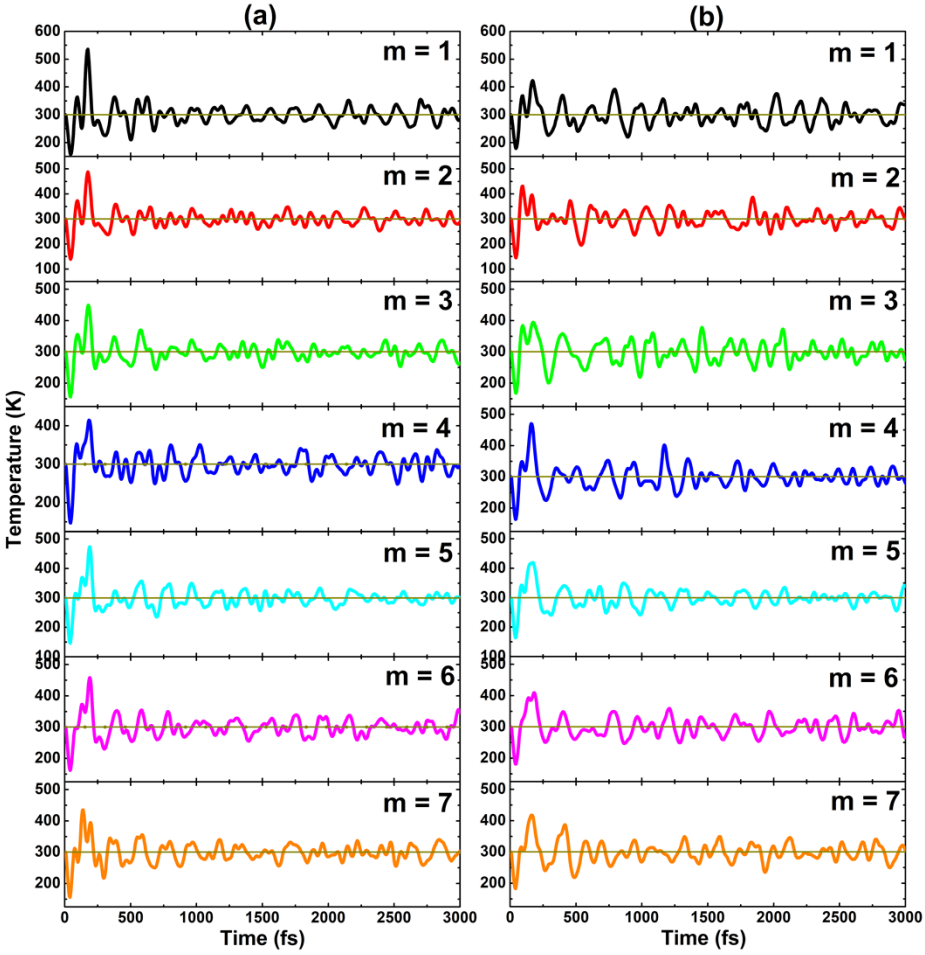

Figure S2: AIMD simulations at 300 K of (a) Armchair- and (b) Zigzag-interline $(Ge)_m$-$(AsSb)_{8-m}$ lateral heterostructures.

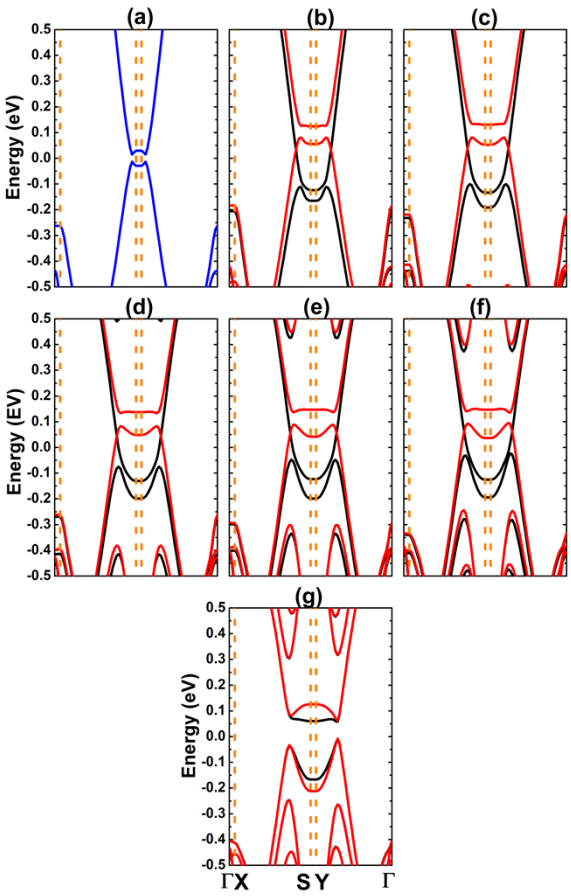

Figure S3: Electronic band structure (B lue curve: non-spin polarization; Black curve: Spin-up; Red curve: Spin-down) of zigzag-interline $(Ge)_m$-$(AsSb)_{8-m}$ lateral heterostructures with (a) m = 1, (b) m = 2, (c) m = 3, (d) m = 4, (e) m = 5, (f) m = 6, and (g) m = 7.